Central™
Semiconductor Corp.
145 Adams Avenue, Hauppauge, NY 11788 USA
Tel: (631) 435-1110 • Fax: (631) 435-1824
www.centralsemi.com
mailto:processchange@centralsemi.com
http://www.centralsemi.com/processchange

PCN #: 129
Notification Date: 5 October 2011

Product / Process Change Notice

Parts Affected:
Chip process CP195, NPN small signal transistors, wafers, and die in chip form.

Extent of Change:
The CP195 wafer process has been discontinued and replaced with the CP318V wafer process. The CP195 chip process measures 30 x 30 mils and the CP318V chip process measures 26 x 26 mils. See Figures 1 and 2 for die geometry.

Reason for Change:
An alternate wafer foundry was approved for NPN small signal transistor processes.

Effect of Change:
This change does not affect the electrical characteristics of any device.

Qualification:
Standard evaluation and qualifications completed resulting in no electrical rejects.

Effective Date of Change:
Existing inventory will be shipped until depleted.

Sample Availability:
Please contact Salesperson or Manufacturer's Representative.

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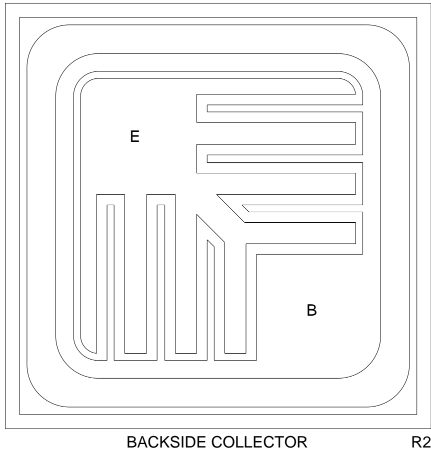
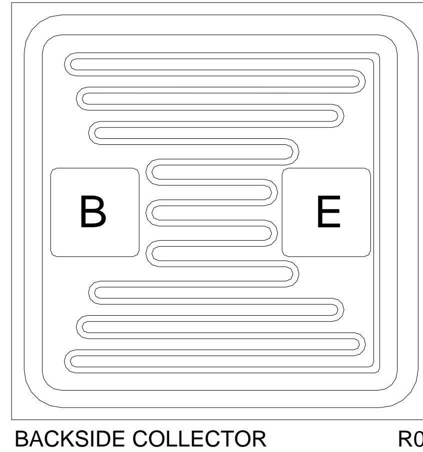
Figures:

Figure 1: CP195 Chip Geometry



Die Size:	30 x 30 mils
Die Thickness:	7.5 mils
Bond Pad Area (Emitter):	8 x 8 mils
Bond Pad Area (Base):	7.2 x 7.2 mils
Topside Metal:	Al (30,000Å)
Backside Metal:	Au (11,000Å)

Figure 2:CP318V Chip Geometry



Die Size:	26 x 26 mils
Die Thickness:	7.1 mils
Bond Pad Area (Emitter):	5.5 x 5.5 mils
Bond Pad Area (Base):	5.5 x 5.5 mils
Topside Metal:	Al-Si (17,000Å)
Backside Metal:	Au (12,000Å)

Part Numbers Affected:

CP195-2N3501-CT
CP195-2N3501-WN
CP195-2N5682-CT
CP195-2N5682-WN
2N3501
2N5682